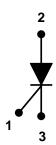
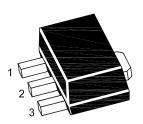
Thyristors





1.Gate 2.Anode 3.Cathode SOT-89 Plastic Package

Absolute Maximum Ratings (T_a= 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Repetitive peak reverse voltage		V_{RRM}	400	V
Non-repetitive peak reverse voltage		V_{RSM}	500	V
Repetitive peak off-state voltage ¹⁾		V_{DRM}	400	V
On-State Current RMS		I _{T(RMS)}	0.79	Α
Average on-state current ²⁾	Ta = 57C°	I _{T (AV)}	0.5	Α
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz)		I _{TSM}	10	А
Circuit Fusing Considerations (t = 8.3 ms)		l ² t	0.4	A^2s
Forward Peak Gate Power		P_GM	0.1	W
Forward Average Gate Power		$P_{G(AV)}$	0. 01	W
Forward Peak Gate Current		I _{FGM}	0.1	Α
Reverse Peak Gate Voltage		V_{RGM}	6	V
Peak gate forward voltage		VFGM	6	V
Operating Junction Temperature Range		T _j	- 40 to + 125	°C
Storage Temperature Range		T _{stg}	- 40 to + 125	°C

 $^{^{1)}}$ With gate to cathode resistance R_{GK} = 1 K Ω .



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Characteristics at T_a= 25 ℃

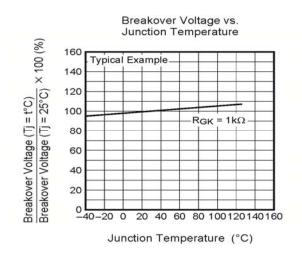
Parameter	Symbol	Min.	Max.	Unit
Peak Repetitive Forward or Reverse Blocking Current at V_{AK} = Rated V_{DRM} and V_{RRM} , R_{GK} = 1 K Ω T_{C} = 125°C	I _{DRM} , I _{RRM}	-	0.1	mA
Peak Forward On-State Voltage at I _{TM} = 1.5 A	V_{TM}	-	1.9	V
Gate Trigger Current at $V_D = 6 \text{ V}$, $I_T = 0.1 \text{A}$	I _{GT}	20	100 ³⁾	μA
Gate Trigger Voltage at $V_D = 6 \text{ V}$, $I_T = 0.1 \text{A}$	V_{GT}	-	0.8	V
Gate Non-Trigger Voltage ¹⁾ at $V_D = 1/2 V_{DRM}$, $R_{GK} = 1 K\Omega$, $T_C = 125^{\circ}C$	V_{GD}	0.2	-	V
Holding Current at V_D = 12 V, R_{GK} = 1 K Ω	I _H	-	3	mA

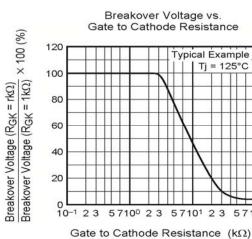
²⁾ Soldering with ceramic plate (25 mm X 25 mm X t0.7 mm).

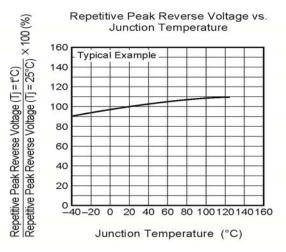
If special values of I_{GT} are required, choose item E from those listed in the table below if possible.

Item	В	E
I _{GT}	20 to 50	20 to 100

The above values do not include the current flowing through the 1 k Ω resistance between the gate and cathode.









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